## ABSTRACT AMENDMENT

Replace the Abstract with:

A via-filling material comprising includes a polymer containing a repeat repeating unit represented by the following formula (1):

$$R_1$$
 $|$ 
 $-CH_2-C$ 
 $|$ 
 $X - R_2$ 

wherein  $R_1$  is a member selected from the group consisting one of hydrogen atom, fluorine atom, chlorine atom, bromine atom, and methyl group;  $R_2$  is a member selected from the group-consisting one of hydrogen atom, a  $C_{1-3}$  alkyl group, and a  $C_{1-4}$  alkyl group in which the hydrogen atom is substituted replaced by at least one kind of atoms of fluorine, chlorine, and bromine atom; and X is -C(=O)O- or  $-S(=O)_2O-$  is used as the via-filling material. This via-filling material does not generate deposition deposits around the an opening part of a via hole during plasma etching and provides a semiconductor integrated circuit with high reliability, even when a trench wider than the via hole is formed by plasma etching around the via hole filled with the via-filling material with plasma.